TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

TC74VCX16501FT

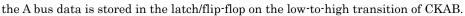
Low-Voltage 18-Bit Universal Bus Transceiver with 3.6-V Tolerant Inputs and Outputs

The TC74VCX16501FT is a high performance CMOS 18-bit universal bus transceiver. Designed for use in 1.8-V, 2.5-V or 3.3-V systems, it achieves high-speed operation while maintaining the CMOS low power dissipation.

It is also designed with overvoltage tolerant inputs and outputs up to $3.6\ V$.

Data flow in each direction is controlled by output-enable (OEAB and \overline{OEBA}), latch-enable (LEAB and LEBA), and clock (CKAB and CKBA) inputs.

For A-to-B data flow, the device operates in the transparent mode when LEAB is high. When LEAB is low, the A data is latched if CKAB is held at a high or low logic level. If LEAB is low,



Data flow for B to A is similar to that of A to B but uses OEBA, LEBA, and CKBA.

When the \overline{OE} input is high, the outputs are in a high-impedance state. This device is designed to be used with 3-state memory address drivers, etc.

All inputs are equipped with protection circuits against static discharge.

Features (Note)

- Low-voltage operation: V_{CC} = 1.8 to 3.6 V
- High-speed operation: $t_{pd} = 2.9 \text{ ns (max) (V}_{CC} = 3.0 \text{ to } 3.6 \text{ V)}$

: $t_{pd} = 3.5 \text{ ns (max) (V}_{CC} = 2.3 \text{ to } 2.7 \text{ V})$

: $t_{pd} = 7.0 \text{ ns (max) (V}_{CC} = 1.8 \text{ V})$

• Output current: $I_{OH}/I_{OL} = \pm 24 \text{ mA (min)} (V_{CC} = 3.0 \text{ V})$

: $I_{OH}/I_{OL} = \pm 18 \text{ mA (min) (V}_{CC} = 2.3 \text{ V)}$

: $I_{OH}/I_{OL} = \pm 6 \text{ mA (min) (V}_{CC} = 1.8 \text{ V)}$

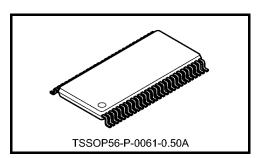
- Latch-up performance: -300 mA
- ESD performance: Machine model $\geq \pm 200 \text{ V}$

Human body model $\geq \pm 2000 \text{ V}$

- Package: TSSOP
- Bidirectional interface between 2.5 V and 3.3 V signals.
- 3.6-V tolerant function and power-down protection provided on all inputs and outputs

Note: Do not apply a signal to any bus pins when it is in the output mode. Damage may result.

All floating (high impedance) bus pins must have their input level fixed by means of pull-up or pull-down resistors.

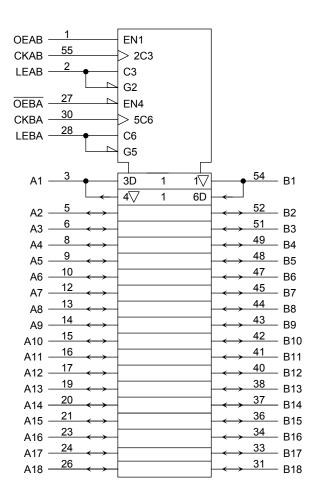


Weight: 0.25 g (typ.)

Pin Assignment (top view)

56 GND OEAB **LEAB** 2 55 **CKAB** Α1 3 54 В1 GND 4 **GND** 53 A2 5 52 В2 АЗ 6 ВЗ 51 7 V_{CC} 50 V_{CC} 8 В4 A4 49 A5 48 В5 A6 10 В6 GND 11 46 **GND** A7 12 В7 45 A8 13 В8 В9 A9 14 43 A10 15 42 B10 A11 16 B11 41 A12 17 B12 GND 18 GND 39 A13 19 38 B13 A14 20 37 B14 A15 21 B15 36 V_{CC} 22 35 V_{CC} A16 23 B16 34 A17 24 33 B17 GND 25 32 **GND** A18 26 31 B18 OEBA 27 **CKBA** LEBA 28 GND 29

IEC Logic Symbol



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Truth Table (A bus → B bus)

	Inputs					
OEAB	LEAB	CKAB	Α	В		
L	Х	X	Х	Z		
Н	Н	Х	L	L		
Н	Н	Х	Н	Н		
Н	L		L	L		
Н	L		Н	Н		
Н	-	Н	Х	В0		
П	L	П	^	(Note)		
Н	_		X	В0		
П	L	L	^	(Note)		

Note: Output level before the indicated steady-state input conditions were established, provided that CKAB was low or high before LEAB went low.

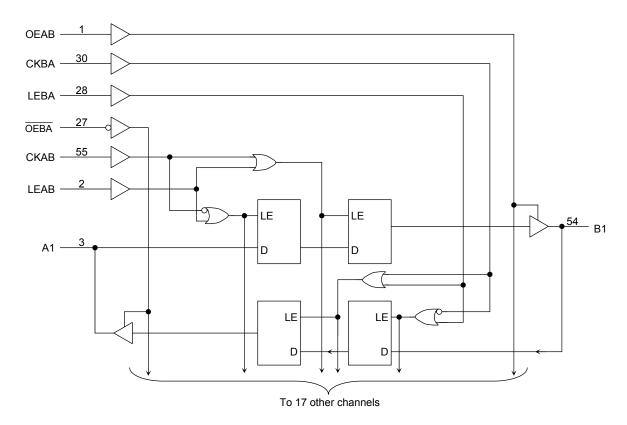
Truth Table (B bus → A bus)

	Inputs					
OEBA	LEBA	CKBA	В	Α		
Н	Х	Х	Х	Z		
L	Н	Х	L	L		
L	Н	Х	Н	Н		
L	L		L	L		
L	L		Н	Н		
		Н	Х	A0		
L	L	П	^	(Note)		
			Х	A0		
Ĺ	L	L	^	(Note)		

Note: Output level before the indicated steady-state input conditions were established, provided that CKBA was low or high before LEBA went low.

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System Diagram



Absolute Maximum Ratings (Note 1)

Characteristics	Symbol	Rating	Unit
Power supply voltage	V _{CC}	-0.5 to 4.6	V
DC input voltage (OEAB, OEBA, LEAB, LEBA, CKAB, CKBA)	V _{IN}	-0.5 to 4.6	٧
		-0.5 to 4.6 (Note 2)	
DC bus I/O voltage	$V_{I/O}$	-0.5 to V _{CC} + 0.5	V
		(Note 3)	
Input diode current	l _{IK}	-50	mA
Output diode current	lok	±50 (Note 4)	mA
DC output current	lout	±50	mA
Power dissipation	P_{D}	400	mW
DC V _{CC} /ground current per supply pin	I _{CC} /I _{GND}	±100	mA
Storage temperature	T _{stg}	-65 to 150	°C

Note 1: Exceeding any of the absolute maximum ratings, even briefly, lead to deterioration in IC performance or even destruction.

Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings and the operating ranges.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 2: OFF state

Note 3: High or low state. IOUT absolute maximum rating must be observed.

Note 4: $V_{OUT} < GND, V_{OUT} > V_{CC}$

Operating Ranges (Note 1)

Characteristics	Symbol	Rating	Unit
Dower cumply voltage	Vaa	1.8 to 3.6	V
Power supply voltage	V _{CC}	1.2 to 3.6 (Note 2)	V
Input voltage (OEAB, OEBA, LEAB, LEBA, CKAB, CKBA)	V _{IN}	-0.3 to 3.6	V
Bus I/O voltage	Viva	0 to 3.6 (Note 3)	V
bus I/O voltage	V _{I/O}	0 to V _{CC} (Note 4)	V
		±24 (Note 5)	
Output current	I _{OH} /I _{OL}	±18 (Note 6)	mA
		±6 (Note 7)	
Operating temperature	T _{opr}	-40 to 85	°C
Input rise and fall time	dt/dv	0 to 10 (Note 8)	ns/V

- Note 1: The operating ranges must be maintained to ensure the normal operation of the device.

 Unused inputs must be tied to either VCC or GND.
- Note 2: Data retention only
- Note 3: OFF state
- Note 4: High or low state
- Note 5: $V_{CC} = 3.0 \text{ to } 3.6 \text{ V}$
- Note 6: $V_{CC} = 2.3 \text{ to } 2.7 \text{ V}$
- Note 7: $V_{CC} = 1.8 \text{ V}$
- Note 8: $V_{IN} = 0.8$ to 2.0 V, $V_{CC} = 3.0$ V

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Electrical Characteristics

DC Characteristics (Ta = -40 to 85°C, 2.7 V < $V_{\text{CC}} \leq 3.6 \text{ V})$

Character	istics	Symbol	Test Condition		V 00	Min	Max	Unit			
	T				V _{CC} (V)	0.0					
Input voltage	H-level	V _{IH}			2.7 to 3.6	2.0	_	V			
	L-level	V _{IL}	-	_	2.7 to 3.6	_	0.8				
				$I_{OH} = -100 \ \mu A$	2.7 to 3.6	V _{CC} - 0.2	_				
	H-level	V _{OH}	V _{IN} = V _{IH} or V _{IL}	$I_{OH} = -12 \text{ mA}$	2.7	2.2	_				
				$I_{OH} = -18 \text{ mA}$	3.0	2.4	_				
Output voltage				$I_{OH} = -24 \text{ mA}$	3.0	2.2	_	V			
				I _{OL} = 100 μA	2.7 to 3.6	_	0.2				
	L-level	\/-·	$V_{IN} = V_{IH} \text{ or } V_{IL}$	I _{OL} = 12 mA	2.7	_	0.4				
	L-ievei	V _{OL}		AIN — AIH OI AIL	 VIN = VIH OI VIL	AIN - AIH OI AIL	I _{OL} = 18 mA	3.0	_	0.4	
				I _{OL} = 24 mA	3.0	_	0.55				
Input leakage curre	ent	I _{IN}	V _{IN} = 0 to 3.6 V		2.7 to 3.6	_	±5.0	μΑ			
0 -1-11-1 055	-1-1	loz	V _{IN} = V _{IH} or V _{IL}		0.74-0.0		140.0	^			
3-state output OFF	3-state output OFF state current		$V_{OUT} = 0$ to 3.6 V		2.7 to 3.6		±10.0	μΑ			
Power-off leakage	current	l _{OFF}	V _{IN} , V _{OUT} = 0 to 3.6 V		0		10.0	μА			
0:		1	V _{IN} = V _{CC} or GND		2.7 to 3.6	_	20.0				
Quiescent supply of	urent	Icc	$V_{CC} \le (V_{IN}, V_{OUT}) \le 3.$	V _{CC} ≤ (V _{IN} , V _{OUT}) ≤ 3.6 V		_	±20.0	μΑ			
Increase in I _{CC} per	input	Δlcc	V _{IH} = V _{CC} - 0.6 V		2.7 to 3.6		750				

DC Characteristics (Ta = -40 to 85°C, 2.3 V \leq V_{CC} \leq 2.7 V)

Characte	ristics	Symbol	Test Condition		V _{CC} (V)	Min	Max	Unit									
	H-level	V _{IH}		_	2.3 to 2.7	1.6	_										
Input voltage	L-level	V _{IL}		_	2.3 to 2.7	_	0.7	V									
				I _{OH} = -100 μA	2.3 to 2.7	V _{CC} - 0.2	_										
	H-level	V _{OH}	V _{IN} = V _{IH} or V _{IL}	I _{OH} = -6 mA	2.3	2.0	_										
													I _{OH} = -12 mA	2.3	1.8	_	
Output voltage				I _{OH} = -18 mA	2.3	1.7	_	V									
			V_{OL} $V_{IN} = V_{IH} \text{ or } V_{IL}$	I _{OL} = 100 μA	2.3 to 2.7	_	0.2										
	L-level	V _{OL}		$V_{IN} = V_{IH} \ or \ V_{IL}$	$V_{IN} = V_{IH}$ or V_{IL}	$V_{IN} = V_{IH} \ or \ V_{IL}$	I _{OL} = 12 mA	2.3	_	0.4							
				I _{OL} = 18 mA	2.3	_	0.6										
Input leakage curre	ent	I _{IN}	V _{IN} = 0 to 3.6 V	•	2.3 to 2.7	_	±5.0	μА									
2 state output OFF	= atata aurrant	la-	V _{IN} = V _{IH} or V _{IL}		2.3 to 2.7		±10.0										
3-state output OFF state current		loz	V _{OUT} = 0 to 3.6 V		2.3 10 2.7	_	±10.0	μΑ									
Power-off leakage	current	loff	V _{IN} , V _{OUT} = 0 to 3.6 V		0		10.0	μА									
Quiescent supply	current		V _{IN} = V _{CC} or GND		2.3 to 2.7		20.0	μА									
Quiescerit Supply (Current	Icc	$V_{CC} \le (V_{IN}, V_{OUT}) \le$	3.6 V	2.3 to 2.7	_	±20.0	μΑ									



DC Characteristics (Ta = -40 to 85°C, 1.8 V \leq V_{CC} < 2.3 V)

Characteris	stics	Symbol	Test Condition			Min	Max	Unit
		Í			V _{CC} (V)			
Input voltage	H-level	V _{IH}	_	_	1.8 to 2.3	0.7 × V _{CC}	_	V
input voitage	L-level	V _{IL}	_	_	1.8 to 2.3		0.2 × V _{CC}	V
	H-level	Voh	V _{IN} = V _{IH} or V _{IL}	I _{OH} = -100 μA	1.8	V _{CC} - 0.2	_	
Output voltage				$I_{OH} = -6 \text{ mA}$	1.8	1.4	_	V
	L-level	\/a.	\\\\\r\\\r\\	I _{OL} = 100 μA	1.8	_	0.2	
	L-level	V _{OL}	$V_{IN} = V_{IH} \text{ or } V_{IL}$	I _{OL} = 6 mA	1.8	_	0.3	
Input leakage currer	nt	I _{IN}	V _{IN} = 0 to 3.6 V		1.8	_	±5.0	μА
3-state output OFF	state current	l _{OZ}	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $V_{OUT} = 0 \text{ to } 3.6 \text{ V}$			_	±10.0	μА
Power-off leakage c	urrent	l _{OFF}	V _{IN} , V _{OUT} = 0 to 3.6 V		0	_	10.0	μА
Quioscont supply of	ırront	laa	V _{IN} = V _{CC} or GND		1.8	_	20.0	^
Quiescent supply cu		Icc	$V_{CC} \le (V_{IN}, V_{OUT}) \le 3.6 \text{ V}$		1.8		±20.0	μА

AC Characteristics (Ta = –40 to 85°C, input: $t_r = t_f$ = 2.0 ns, C_L = 30 pF, R_L = 500 Ω) (Note 1)

Characteristics Symbol Test Condition		Min	Max	Unit		
	5,55.	. cot condition	V _{CC} (V)			0
			1.8	100		
Maximum clock frequency	f _{max}	Figure 1, Figure 3	2.5 ± 0.2	200	_	MHz
			3.3 ± 0.3	250	_	
Draw and in dalay time			1.8	1.5	7.0	
Propagation delay time	t _{pLH}	Figure 1, Figure 2	2.5 ± 0.2	0.8	3.5	ns
(An, Bn-Bn, An)	tpHL		3.3 ± 0.3	0.6	2.9	
Description delections			1.8	1.5	8.8	
Propagation delay time	t _{pLH}	Figure 1, Figure 3	2.5 ± 0.2	0.8	4.4	ns
(CKAB, CLKBA-Bn, An)	tpHL		3.3 ± 0.3	0.6	3.5	
			1.8	1.5	9.8	
Propagation delay time	t _{pLH}	Figure 1, Figure 4	2.5 ± 0.2	0.8	4.9	ns
(LEAB, LEBA-Bn, An)	tpHL		3.3 ± 0.3	0.6	3.8	
0.1.1.11.5		Figure 1, Figure 5, Figure 6	1.8	1.5	9.8	
Output enable time	t _{pZL}		2.5 ± 0.2	0.8	4.9	ns
(OEAB, OEBA -Bn, An)	t _{pZH}		3.3 ± 0.3	0.6	3.8	
		Figure 1, Figure 5, Figure 6	1.8	1.5	7.6	
Output disable time	t _{pLZ}		2.5 ± 0.2	0.8	4.2	ns
(OEAB, OEBA -Bn, An)	t _{pHZ}		3.3 ± 0.3	0.6	3.7	
	1,		1.8	4.0	_	
Minimum pulse width	tw (H)	Figure 1, Figure 3, Figure 4	2.5 ± 0.2	1.5	_	ns
	t _{W (L)}		3.3 ± 0.3	1.5	_	
			1.8	2.5	_	
Minimum set-up time	t _s	Figure 1, Figure 3, Figure 4	2.5 ± 0.2	1.5	_	ns
			3.3 ± 0.3	1.5	_	
			1.8	1.0	_	
Minimum hold time	t _h	Figure 1, Figure 3, Figure 4	2.5 ± 0.2	1.0	_	ns
			3.3 ± 0.3	1.0	_	
			1.8	_	0.5	
Output to output skew	tosLH	(Note 2)	2.5 ± 0.2	_	0.5	ns
	tosHL		3.3 ± 0.3	_	0.5	

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Note 1: For $C_L = 50$ pF, add approximately 300 ps to the AC maximum specification.

Note 2: Parameter guaranteed by design. $(t_{OSLH} = |t_{DLHm} - t_{DLHn}|, t_{OSHL} = |t_{DHLm} - t_{DHLn}|)$



Dynamic Switching Characteristics

(Ta = 25°C, input: $t_r = t_f = 2.0 \text{ ns}, C_L = 30 \text{ pF}, R_L = 500 \Omega$)

Characteristics	Symbol	Test Condition			Тур.	Unit
Characteristics	Symbol			V _{CC} (V)	τyp.	Offic
		$V_{IH} = 1.8 \text{ V}, V_{IL} = 0 \text{ V}$ (N	Note)	1.8	0.25	
Quiet output maximum dynamic V _{OL}	V _{OLP}	$V_{IH} = 2.5 \text{ V}, V_{IL} = 0 \text{ V}$ (N	Note)	2.5	0.6	V
		$V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$ (N	Note)	3.3	0.8	
	V _{OLV}	$V_{IH} = 1.8 \text{ V}, V_{IL} = 0 \text{ V}$ (N	Note)	1.8	-0.25	
Quiet output minimum dynamic V _{OL}		$V_{IH} = 2.5 \text{ V}, V_{IL} = 0 \text{ V}$ (N	Note)	2.5	-0.6	V
<u></u>		$V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$ (N	Note)	3.3	-0.8	
Quiet output minimum dynamic	V _{OHV}	$V_{IH} = 1.8 \text{ V}, V_{IL} = 0 \text{ V}$ (N	Note)	1.8	1.5	
		$V_{IH} = 2.5 \text{ V}, V_{IL} = 0 \text{ V}$ (N	Note)	2.5	1.9	V
···		$V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$ (N	Note)	3.3	2.2	

Note: Parameter guaranteed by design.

Capacitive Characteristics (Ta = 25°C)

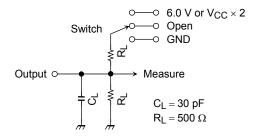
Characteristics	Symbol	Symbol Test Condition		Tun	Unit
Characteristics	Syllibol	rest Condition	V _{CC} (V)	Тур.	Offic
Input capacitance	C _{IN}	_	1.8, 2.5, 3.3	6	pF
Bus I/O capacitance	C _{I/O}	_	1.8, 2.5, 3.3	7	pF
Power dissipation capacitance	C _{PD}	f _{IN} = 10 MHz (Note)	1.8, 2.5, 3.3	20	pF

Note: C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

 $I_{CC (opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/18 \text{ (per bit)}$

AC Test Circuit



Parameter	Switch			
t _{pLH} , t _{pHL}	Open			
t _{pLZ} , t _{pZL}	$ \begin{array}{cccccccccccccccccccccccccccccccccccc$			
t _{pHZ} , t _{pZH}	GND			

Figure 1

AC Waveform

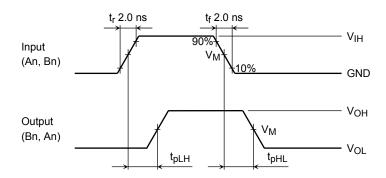


Figure 2 t_{pLH}, t_{pHL}

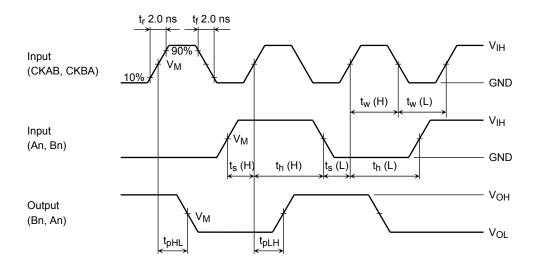


Figure 3 t_{pLH} , t_{pHL} , t_w , t_s , t_h

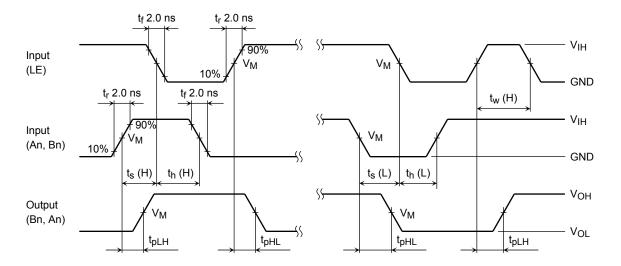


Figure 4 t_{pLH}, t_{pHL}, t_w, t_s, t_h

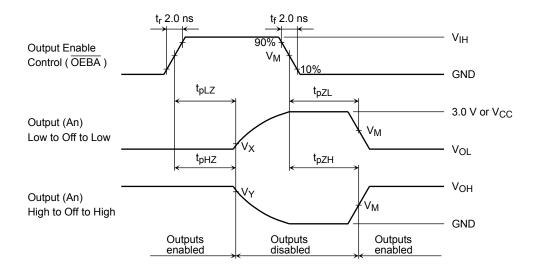
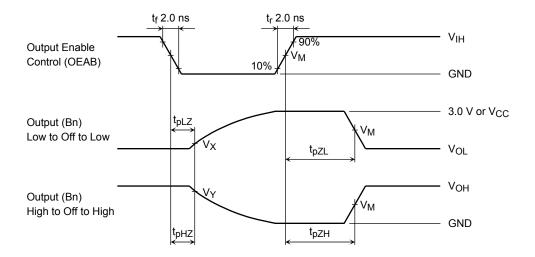


Figure 5 t_{pLZ} , t_{pHZ} , t_{pZL} , t_{pZH}

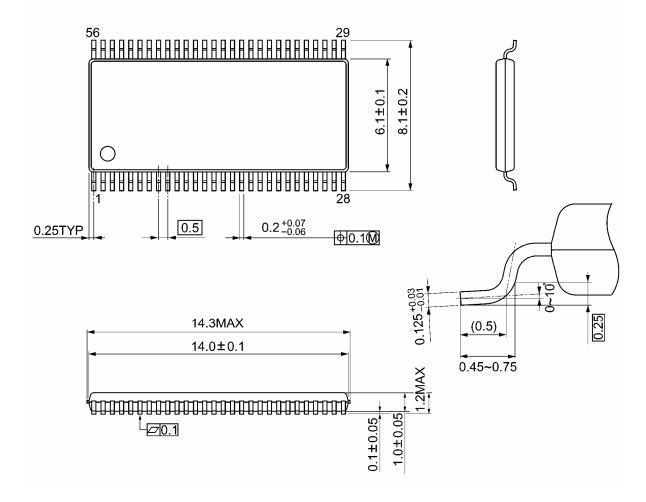


 $\textbf{Figure 6} \quad t_{\text{pLZ}}, t_{\text{pHZ}}, t_{\text{pZL}}, t_{\text{pZH}}$

Symbol		V _{CC}	
Syllibol	$3.3\pm0.3~\textrm{V}$	$2.5\pm0.2\textrm{V}$	1.8 V
V_{IH}	2.7 V	V _{CC}	V _{CC}
V _M	1.5 V	V _{CC} /2	V _{CC} /2
VX	V _{OL} + 0.3 V	V _{OL} + 0.15 V	V _{OL} + 0.15 V
VY	V _{OH} – 0.3 V	V _{OH} – 0.15 V	V _{OH} – 0.15 V

Package Dimensions

TSSOP56-P-0061-0.50A Unit: mm



Weight: 0.25 g (typ.)

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20070701-EN GENERAL

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